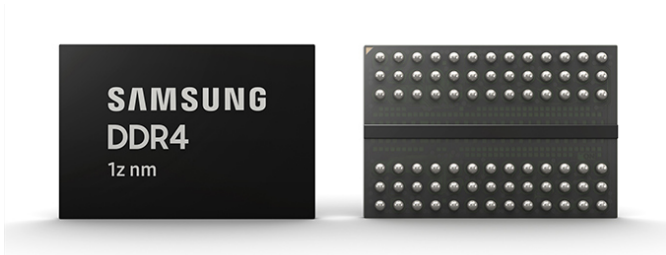


Samsung announces the development of an industry first-- 3rd generation 10-nanometer class (aka 1z-nm) 8Gb DDR4 DRAM, the smallest process node for memory produced without need for extreme ultraviolet lithography (EUVL).



Set for mass production within H2 2019, the 1z-nm process allows Samsung to make 20% more 8Gb DDR4 chips per wafer compared to the 2nd generation 10nm process (aka 1y-nm). An increase in the dies per wafer means the 8Gb DDR4 memory produced is around 20% smaller than the previous generation, bringing about a decrease in production costs and, ultimately, cheaper DRAM prices on the consumer side.

“Our commitment to break through the biggest challenges in technology has always driven us toward greater innovation. We are pleased to have laid the groundwork again for stable production of next-generation DRAM that ensures the highest performance and energy efficiency,” Samsung says. “As we build out our 1z-nm DRAM lineup, Samsung is aiming to support its global customers in their deployment of cutting-edge systems and enabling proliferation of the premium memory market.”

The first 1z-nm products will go for applications including servers, graphics and mobile devices.

Go [Samsung Develops Industry's First 3rd-generation 10nm-Class DRAM for Premium Memory Applications](#)